

This Sheet Has Been Replaced



THIS SHEET HAS BEEN
REPLACED

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICES

ABSTRACT OF THE DISCLOSURE

On a silicon substrate, a silicon oxide layer, a first platinum layer, a dielectric film and a second platinum layer are formed, and then the second platinum layer and the dielectric film are dry etched, via a resist layer, in a 1-5 Pa low pressure region with a mixed gas of HBr and O_2 as the etching gas. As soon as the first platinum layer is exposed, the unetched portion of dielectric film is etched off in a 5-50 Pa high pressure region, and then the first platinum layer is dry etched again in the low pressure region to form a capacitor consisting of a top electrode, a capacitance insulation layer and a bottom electrode in a semiconductor integrated circuit chip. Using this manufacturing method prevents the deterioration in definition caused by the use of a thick resist and the operation failure of circuit elements such as transistors due to over etching on the insulation layer.

"Fig. 1 to accompany the abstract when published"